

Description

The GM28C4100A high performance read only memory is organized as 524,288 x 8 bit (Byte Mode) or as 262,144 x 16 bit (Word Mode) followed by BHE mode select. The GM23C4100A offers automatic power down controlled by the mark programmed \overline{CE} or CE input. The low power feature allows the battery operation. The large size of 4M bit memory density is ideal for character generator, data or program memory in microprocessor application. This ROM is packaged in 40 pin DIP.

Features

- Switchable Organization
 Byte Mode : 524,188 x 8 bit
 Word Mode : 262,144 x 16 bit
- Single + 5V Supply
- Access Time : 120/150ns (Max)
- Operating current : 50mA (Max)
- Standby current : 50µA (Max)
- TTL-compatible inputs and outputs
- Polarity programmable chip enable and out enable pin
- Byte or Word switchable by BHE pin
 (BHE can be switched on the fly or a DC signal)
- Fully static operation
- Fully static operation
- Package :
 GM23C41000A : 40 Pin Plastic DIP (600 mil)

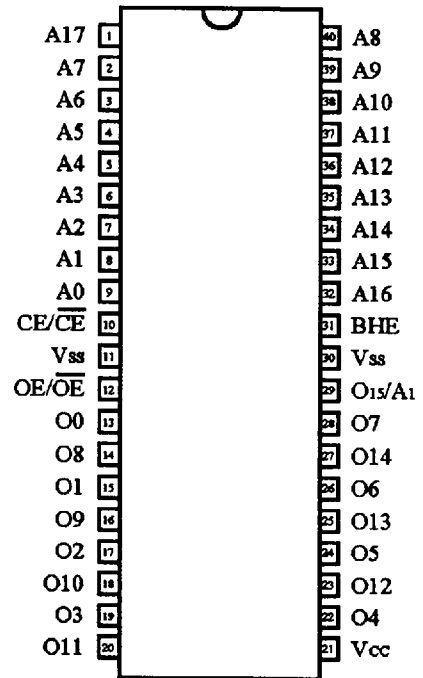
Pin Description

| Pin | Function |
|----------------------|--|
| A0-A17 | Address Inputs |
| O0-O14 | Data Outputs |
| O15/A-1 | Output O15 (Word Mode)/ LSB Address (Byte Mode) |
| BHE | Word/Byte Selection |
| \overline{CE}/CE^* | Chip Enable Input |
| \overline{OE}/OE^* | Output Enable Input |
| Vcc | Power Supply (+5V) |
| Vss | Ground |
| NC | No Connection |

*User Selectable Polarity.

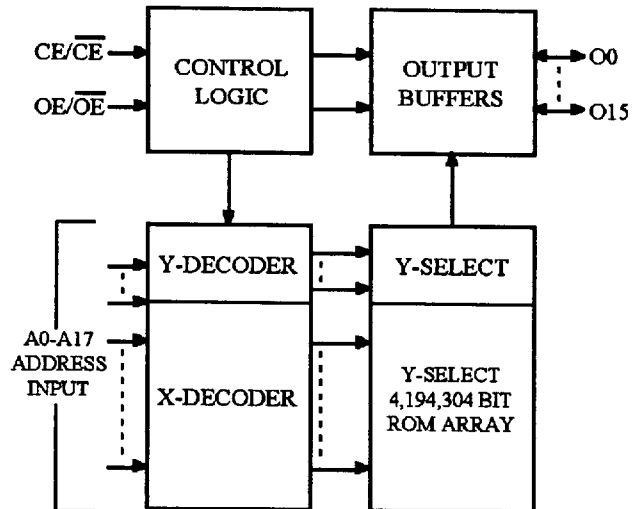
Pin Configuration

40 DIP



(Top View)

Block Diagram



Absolute Maximum Ratings*

| Symbol | Parameter | Rating | Unit |
|------------------|------------------------------------|------------------------------|------|
| T _A | Ambient Operating Temperature | -10 ~ 80 | °C |
| T _{STG} | Storage Temperature | -65 ~ 150 | °C |
| V _{CC} | Supply Voltage to Ground Potential | -0.5 ~ V _{CC} + 0.5 | V |
| V _{OUT} | Output Voltage | -0.5 ~ V _{CC} + 0.5 | V |
| V _{IN} | Input Voltage | -0.5 ~ 7.0 | V |

***Comments**

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only. Functional operation of this device at these or any other conditions above those indicated in the operational sections of this specification is not implied and exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Recommended DC Operating Conditions (V_{CC} = 5.0V ± 10%, T_A = 0 ~ 70°C)

| Symbol | Parameter | Min | Typ | Max | Unit |
|-----------------|--------------------|------|-----|-----------------------|------|
| V _{CC} | Supply Voltage | 4.5 | 5.0 | 5.5 | V |
| V _{SS} | Supply Voltage | 0 | 0 | 0 | V |
| V _{IH} | Input High Voltage | 2.2 | - | V _{CC} + 0.3 | V |
| V _{IL} | Input Low Voltage | -0.3 | - | 0.8 | V |

DC Electrical Characteristics (V_{CC} = 5.0V ± 10%, T_A = 0 ~ 70°C)

| Symbol | Parameter | Condition | Min | Typ | Max | Unit |
|-------------------|---|--|-----|-----|------|------|
| V _{OH} | Output High Voltage | I _{OH} = -1mA | 2.4 | | | V |
| V _{OL} | Output Low Voltage | I _{OL} = 3.2mA | | | 0.4 | V |
| I _{I(L)} | Input Leakage Current | V _{IN} = 0V to V _{CC} | | | ± 10 | μA |
| I _{O(L)} | Output Leakage Current | V _{OUT} = 0V to V _{CC} | | | ± 10 | μA |
| I _{CC} | Operating Supply Current (f = 6.7 MHz) | $\overline{CE} = V_{IL}, CE = V_{IH}$ | | | 50 | mA |
| I _{SB1} | Standby Current (TTL) | $\overline{CE} = V_{IH}$, all Output Open | | | 1 | mA |
| I _{SB2} | Standby Current (CMOS) | $\overline{CE} = V_{CC}$, all Output Open | | | 50 | μA |

Capacitance (T_A = 25°C, f = 1.0 MHz)

| Symbol | Parameter | Condition | Min | Max | Unit |
|----------------|--------------------|-----------------------|-----|-----|------|
| C _I | Input Capacitance | V _{IN} = 0V | | 10 | pF |
| C _O | Output Capacitance | V _{OUT} = 0V | | 10 | pF |

Note : Capacitance is periodically sampled and not 100% tested.

Mode Selection

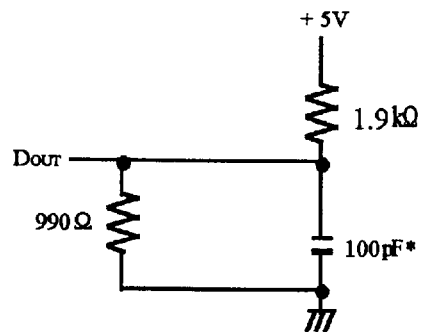
| Mode | CE/ \overline{CE} | OE/ \overline{OE} | BHE | O0~07 | O8~014 | O15/A-1 | Power |
|------------------|---------------------|---------------------|-----|------------------------|--------|---------|---------|
| Standby | L/H | X | X | High-Z | | | Standby |
| 16 Bit Operating | H/L | H/L | H | Data Out | | | Active |
| 8 Bit Operating | | | L | Data Out (Lower 8 Bit) | High-Z | L | |
| | | | | Data Out (Upper 8 Bit) | | H | |
| Output Disable | | | L/H | X | High-Z | | |

AC Operating Characteristics ($V_{CC} = 5.0V \pm 10\%$, $T_A = 0 \sim 70^\circ C$)

| Symbol | Parameter | GM23C4100A-12 | | GM23C4100A-15 | | Unit |
|------------------------|---|---------------|-----|---------------|-----|------|
| | | Min | Max | Min | Max | |
| t_{RC} | Read Cycle Time | 120 | | 150 | | ns |
| t_{ACE} | Chip Enable Access Time | | 120 | | 150 | ns |
| t_{AA} | Address Access Time | | 120 | | 150 | ns |
| t_{AOE} | Output Enable Access Time | | 50 | | 70 | ns |
| t_{OH} | Output Hold From Address Change | 10 | | 10 | | ns |
| t_{OHZ} t_{CHZ} | Output or Chip Disable to Output High-Z | | 50 | | 60 | ns |
| t_{OLZ} t_{CLZ} | Output or Chip Enable to Output Low-Z | 10 | | 10 | | ns |

AC Test Condition

| | |
|-------------------------------|--------------|
| Input Pulse Level | 0.4V to 2.4V |
| Input Rise and Fall Time | 10ns |
| Input and Output Timing Level | 0.8V to 2.0V |
| Output Load | See Fig. 1 |



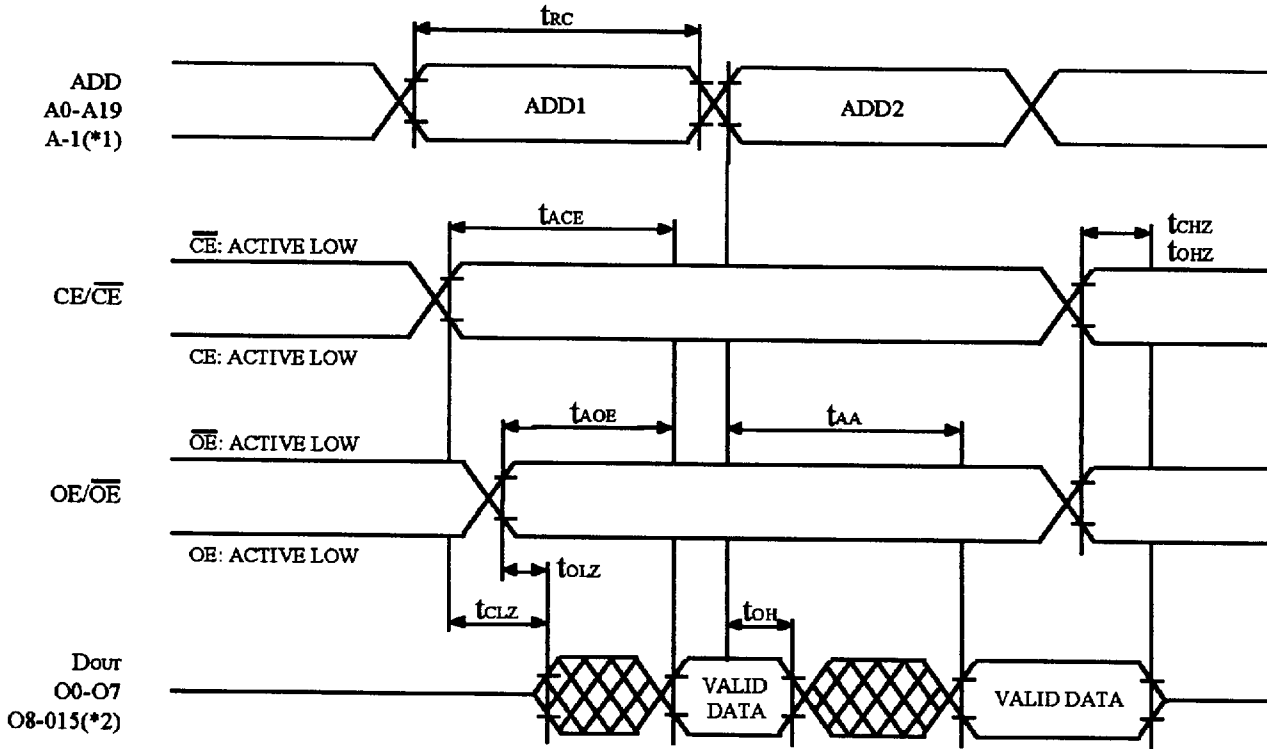
*Including scope and jig.

Fig. 1 Output Load Circuit

Timing Waveforms

Read

Word Mode (BHE=V_{IH}) / Byte Mode (BHE=V_{IL})



(*1) Byte Mode only. A-1 is Keast Significant Bit Address. (BHE = V_{IL})

(*2) Word Mode only. (BHE = V_{IL})

Package Dimensions

Unit: Inches (mm)

40 DIP

